

Silicon NPN Power Transistors

2SC2027

DESCRIPTION

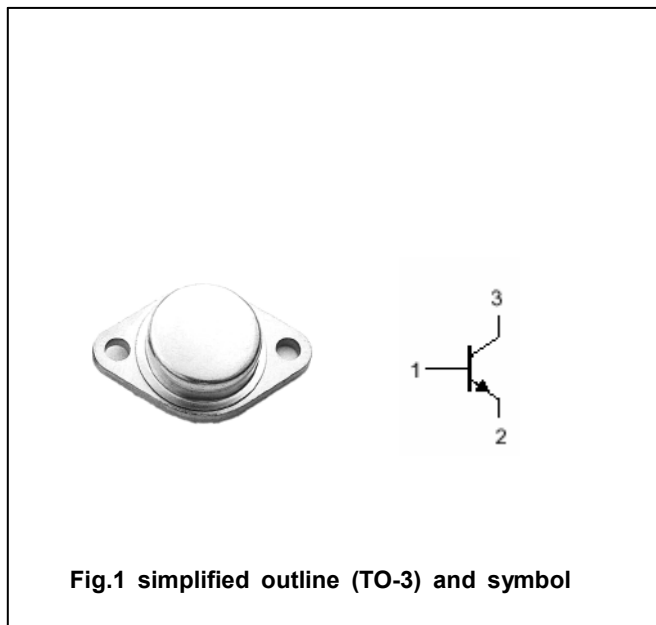
- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- For high voltage ,power switching and TV horizontal output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings(Ta=□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		5	A
I _{CM}	Collector current-peak		7.5	A
P _T	Total power dissipation	T _C =25□	50	W
T _j	Junction temperature		175	□
T _{stg}	Storage temperature		-65~200	□

Silicon NPN Power Transistors

2SC2027

CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A; I _B =0	800			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4.0 A; I _B =1.3 A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4.0 A; I _B =1.3 A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =600V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	8		36	
h _{FE-2}	DC current gain	I _C =4.5A ; V _{CE} =5V	2.25			

PACKAGE OUTLINE

